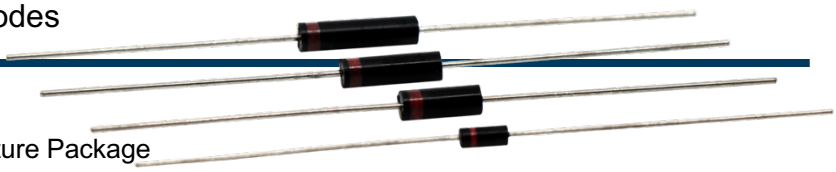
XNV SERIES

2 to 5kV, 120 to 250mA, 70nS
XOE Axial Lead Diodes



Features

- High Voltage, Higher Current Diodes in Subminiature Package
- Utilizes DTI's High Performance XOE™ Technology
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material

Specifications[1]

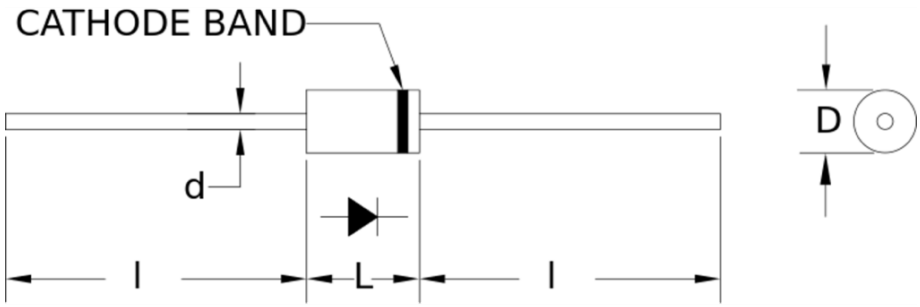
Part Number	V_{RRM} V	I_{FAVM1} mA	I_{FAVM2} mA	V_F V	I_R µA	I_{FSM} A	C_J[2] pF	T_{RR} nS	$R_{\theta JA}$ °C/W	E_{RSM} mJ	L in.	D in.	d in.	l in.
XNV02	2000	250	130	5.4	0.02	5	2.8	70	150	30	0.12	0.08	0.02	1.0
XNV03	3000	200	100	7.1	0.02	5	2.3	70	150	40	0.12	0.08	0.02	1.0
XNV04	4000	160	80	9.1	0.02	5	1.7	70	150	50	0.12	0.08	0.02	1.0
XNV05	5000	120	60	10.3	0.02	5	1.4	70	150	60	0.12	0.08	0.02	1.0

Temperature °C	
Operating Temperature	-55 to 125
Storage Temperature	-55 to 175
Maximum Junction Temperature	125

[1]25°C ambient temperature unless stated otherwise.

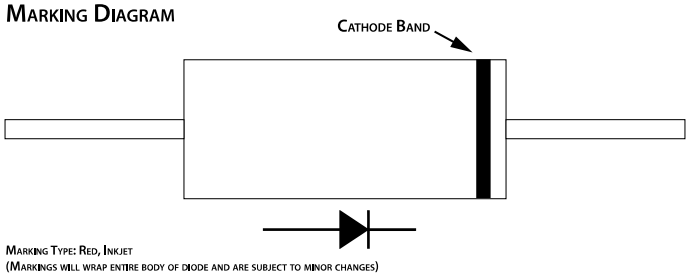
[2]Check Specification Definitions for conditions details.

Drawings



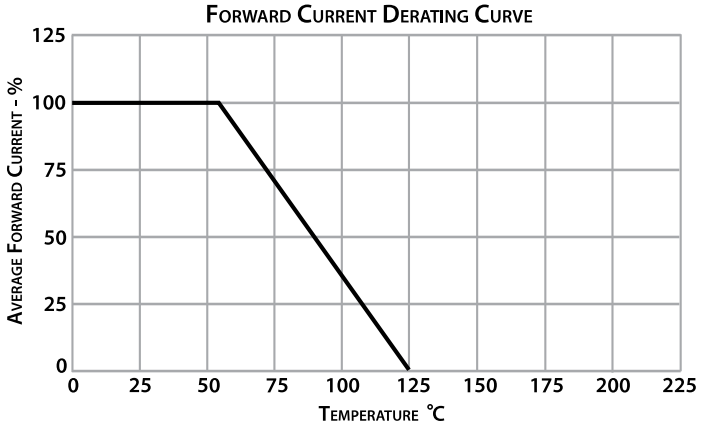
Dimensions in inches, tolerances ±0.020 except as noted

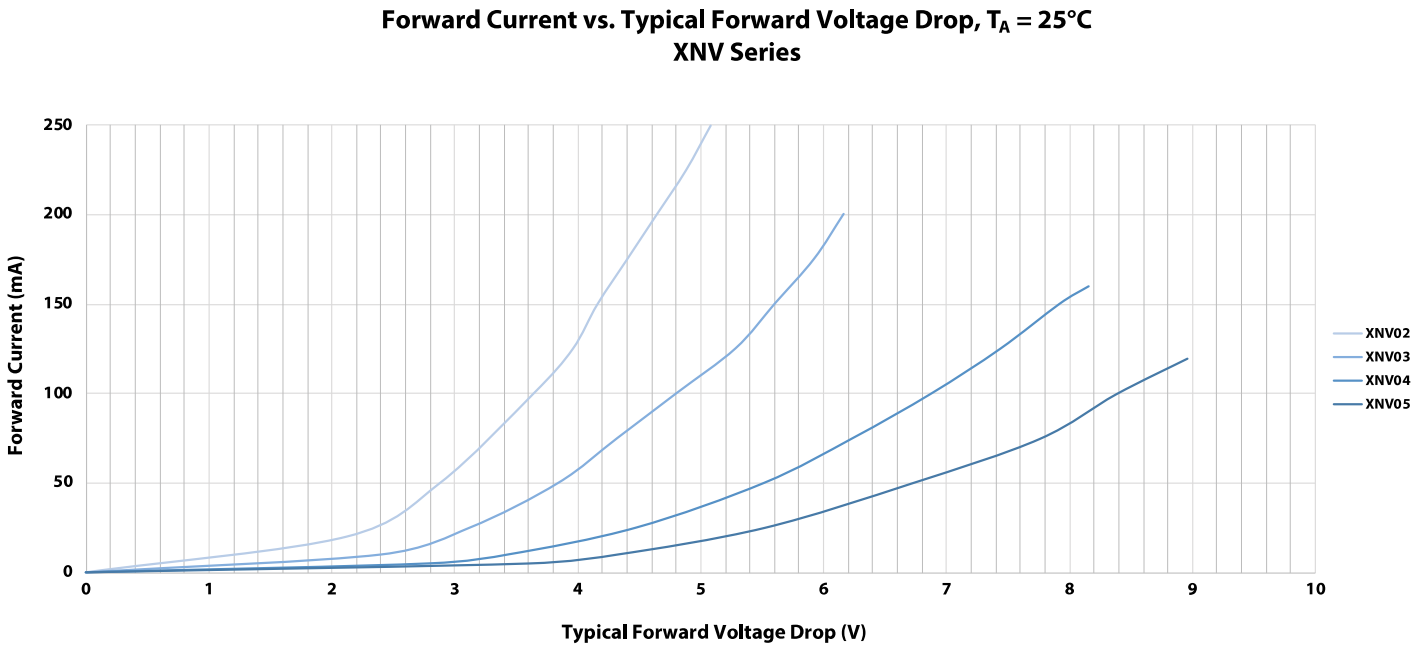
Marking Diagram



Marking Type: Red, Inkjet
(Markings will wrap entire body of diode and are subject to minor changes)

Forward Current Derating Curve





Specification Definitions

	Specifications	Conditions
V_{RRM}	Maximum Repetitive Reverse Voltage	-
I_{FAVM1}	Maximum Average Forward Current	At T_A = 55°C, in Oil
I_{FAVM2}	Maximum Average Forward Current	At T_A = 55°C
V_F	Maximum Forward Voltage Drop	At I_{FAVM1}, t_{PW} = 100µsec
I_R	Maximum Leakage Current	At V_{RRM}
I_{FSM}	Maximum Surge Current	At 8.3mS, Single Half Sine
C_J	Typical Junction Capacitance	At V_R = 4VDC, f = 1MHz
T_{RR}	Maximum Reverse Recovery Time	I_F = 0.5 I_{FAVM1}; I_R = -I_{FAVM1}; I_{RR} = -0.25 I_{FAVM1}
$R_{\theta JA}$	Typical Thermal Resistance	Junction to Ambient, in Air
E_{RSM}	Maximum Reverse Energy Withstand	-

Note: Specifications subject to change without notice. Photo is representation only.

RoHS COMPLIANT